

**REMARKS**

Claims 44, 47-56, 59, 60, 62 and 63 are pending in this application. By this Amendment, claims 50-56 are amended to correct for various informalities and to clarify claims 50-56. Reconsideration based on the above amendments and following remarks is respectfully requested.

Applicants note with appreciation the allowance of claims 44, 47-49, 59, 60, 62 and 63. Applicants respectfully submit that all pending claims are in condition for allowance.

Applicants appreciate the courtesies shown to Applicants' representative by Examiner Prenty in the February 27, 2004 personal interview. Applicants' separate record of the substance of the interview is incorporated into the following remarks.

**I. Claims 52-56 Satisfy the Requirements of 35 U.S.C. §112, Second Paragraph**

The Office Action rejects claims 52-56 under 35 U.S.C. §112, second paragraph, for various informalities. Claims 52-56 have been amended to obviate the rejection. Further, claims 50 and 51 have been amended to be consistent with the changes made to claims 52-56.

As agreed by Examiner Prenty at the February 27 personal interview, the amended claims 52-56 overcome the 35 U.S.C. §112, second paragraph, rejection. Thus, Applicants respectfully request that the 35 U.S.C. §112, second paragraph, rejection be withdrawn.

**II. Claims 50-56 Define Patentable Subject Matter**

The Office Action rejects claims 50-56 under 35 U.S.C. §102(e) over U.S. Patent No. 6,144,041 to Yamazaki et al. (hereinafter "Yamazaki"). The rejection is respectfully traversed.

As agreed by Examiner Prenty at the February 27 personal interview, Yamazaki does not disclose, teach or suggest the feature "adjacent identical-conductive-type source-drain regions of adjacent thin film transistors having the same conductivity type being connected by

respective said radiating extension" set forth in independent claims 50-56. Support for this feature is found in the specification, at least at page 17, line 21 to page 18, line 20, and in Fig. 6.

Further, Yamazaki does not disclose, teach or suggest "source-drain wiring layer connecting the adjacent source-drain regions of adjacent thin film transistors having the same conductivity type" as set forth in independent claim 52. Support for this feature is found in the specification, at least at page 17, lines 1-11, and in Fig. 6.

In contrast, Yamazaki, at least in Figs. 7B and 8A-8D, and at col. 19, line 24 to col. 20, line 67, discloses adjacent source-drain regions 815 and 816 of adjacent thin film transistors PTFT (p-channel thin-film transistor) and NTFT (n-channel thin-film transistor), that have an inverse conductivity type from each other, being connected by radiating extension, e.g. drain electrode 824.

For at least these reasons, it is respectfully submitted that independent claims 50-56 are patentable over the applied art. Withdrawal of the rejection under 35 U.S.C. §102(e) is respectfully requested.

### **III. Conclusion**

In view of the foregoing, it is respectfully submitted that this application is in condition for allowance. Favorable reconsideration and prompt allowance of claims 50-56 are earnestly solicited.

Should the Examiner believe that anything further would be desirable in order to place this application in even better condition for allowance, the Examiner is invited to contact the undersigned at the telephone number set forth below.

Respectfully submitted,



James A. Oliff  
Registration No. 27,075

George P. Simion  
Registration No. 47,089

JAO:GPS/jam

Date: February 27, 2004

**OLIFF & BERRIDGE, PLC**  
**P.O. Box 19928**  
**Alexandria, Virginia 22320**  
**Telephone: (703) 836-6400**

<p>DEPOSIT ACCOUNT USE AUTHORIZATION Please grant any extension necessary for entry; Charge any fee due to our Deposit Account No. 15-0461</p>
--